



News Release

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For Immediate Release

Central's UltraMOS™ MOSFETs expands to 800 volts



Hauppauge, NY USA – April 12, 2016 – Central Semiconductor introduces its newest energy efficient, high voltage UltraMOS™ MOSFET designed to minimize total conduction losses while maximizing power density. The CDM22012-800LRFP is a 12A, 800V MOSFET in the TO-220FP (Full Pack) package. The low $r_{DS(ON)}$ of 0.37Ω and low total gate charge of $7.6nC$ are key energy efficiency characteristics of this UltraMOS™ device, which surpass the operational performance of similarly rated standard MOSFETs. Full specifications are available at: www.centralsemi.com/ultramos

The 800V UltraMOS™ MOSFETs are ideal for power supplies, power inverters and the perfect pairing with Central's HyperFast rectifiers, to provide a superior high speed operational benefit for phase shift compensation in Power Factor Correction (PFC) applications. UltraMOS™ devices are available in industry standard packages as well as in custom packages.

Pricing for the CDM22012-800LRFP is \$1.90 each for 1,000 pieces packed in sleeves or supplied bulk and available from Digi-Key (www.digikey.com) Future Electronics (www.futureelectronics.com) and Mouser Electronics (www.mouser.com). Sample devices are available upon request direct from Central Semiconductor (www.centralsemi.com). In addition to the 800V device, Central has 600V and 700 UltraMOS™ devices available. A 6A, 800V device is also planned for release later this year.

Central Semiconductor Corp. manufactures innovative discrete semiconductors to meet design engineers' ever changing challenges. Specifications for all UltraMOS™ devices can be found on Central's website at: www.centralsemi.com/ultramos

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